

In The Claims

Please cancel claims 1-31 without prejudice, and add new claims 32-48.

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32. A method comprising cleaning an accumulated deposition from a vaporization surface of a vapor forming device by using the vaporization surface as an electrode to form a plasma within the device.

33. The method of claim 32 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

34. The method of claim 32 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

35. The method of claim 32 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.

36. The method of claim 32 wherein the plasma comprises one or more of gaseous Cl₂, CCl₄ and CF₄.

37. The method of claim 32 wherein the device is comprised by a chemical vapor deposition apparatus.

38. A method of cleaning a vaporization surface having deposits accumulated from use in a vapor forming device, the method comprising using the vaporization surface as an electrode to form a plasma within the device, the plasma cleaning at least some of the deposits from the vaporization surface.

39. The method of claim 38 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

40. The method of claim 38 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

41. The method of claim 38 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.

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42. A method comprising:
flowing at least one liquid across a vaporization surface to form a vapor;
accumulating a deposition on the vaporization surface as a vapor is formed therefrom; and
using the vaporization surface as an electrode to form a plasma cleaning at least some of the deposition from the vaporization surface.

43. The method of claim 42 wherein the vaporization surface is comprised by a vapor forming device of a chemical vapor deposition apparatus.

44. The method of claim 42 wherein the vaporization surface is comprised by a chemical vapor deposition apparatus, wherein the at least one liquid comprises $\text{Ba}(\text{THD})_2$, $\text{Sr}(\text{THD})_2$ and $\text{Ti}(\text{THD})_2(\text{O-iPr})_2$, and further comprising chemical vapor depositing BST on a substrate within the apparatus.

46. The method of claim 42 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

47. The method of claim 42 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

48. The method of claim 42 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.

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